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(54) Title: GROWTH OF VERY UNIFORM SILICON CARBIDE EPITAXIAL LAYERS			
(57) Abstract			
<p>An improved chemical vapor deposition method is disclosed that increases the uniformity of silicon carbide epitaxial layers and that is particularly useful for obtaining thicker epitaxial layers. The method comprises heating a reactor to a temperature at which silicon carbide source gases will form an epitaxial layer of silicon carbide on a substrate in the reactor; and then directing a flow of source and carrier gases through the heated reactor to form an epitaxial layer of silicon carbide on the substrate with the carrier gases comprising a blend of hydrogen and a second gas in which the second gas has a thermal conductivity that is less than the thermal conductivity of hydrogen so that the source gases deplete less as they pass through the reactor than they would if hydrogen is used as the sole carrier gas.</p>			

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## GROWTH OF VERY UNIFORM SILICON CARBIDE EPITAXIAL LAYERS

### Field of the Invention

The present invention relates to the epitaxial growth of silicon carbide, and in particular relates to a method of chemical vapor deposition that produces very uniform epitaxial layers of silicon carbide on appropriate substrates.

### Background of the Invention

The present invention relates to the growth of silicon carbide epitaxial layers. As a semiconductor material, silicon carbide is particularly superior for high power, high frequency, and high temperature electronic devices. Silicon carbide has an extremely high thermal conductivity, and can withstand both high electric fields and high current densities before breakdown. Silicon carbide's wide band gap results in low leakage currents even at high temperatures. For these and other reasons, silicon carbide is a quite desirable semiconductor material for power devices; *i.e.*, those designed to operate at relatively high voltages.

Silicon carbide is, however, a difficult material to work with. Growth processes must be carried out at relatively high temperatures, above at least about 1500° C for epitaxial growth and approximately 2200° C for sublimation growth. Additionally, silicon carbide can form over 150 polytypes, many of which are separated by small thermodynamic differences. As a result, single crystal growth of silicon carbide, either by epitaxial layer or bulk crystal, is a challenging process. Finally, silicon carbide's extreme hardness (it is most often industrially used as an abrasive material) contributes to the difficulty in handling it and forming it into appropriate semiconductor devices.

Nevertheless, over the last decade much progress has been made in growth techniques for silicon carbide and are reflected, for example, in U.S. Patents Nos. 4,912,063; 4,912,064; Re.34,861; 4,981,551; 5,200,022; and 5,459,107, all of which are either assigned, or exclusively licensed, to the assignee of the present invention. These and other patents that are commonly assigned with the present invention have sparked worldwide interest in growth techniques for silicon carbide and thereafter the production of appropriate semiconductor devices from silicon carbide.

One particular growth technique is referred to as "chemical vapor deposition" or "CVD." In this technique, source gases (such as silane  $\text{SiH}_4$  and propane  $\text{C}_3\text{H}_8$  for silicon carbide) are introduced into a heated reaction chamber that also includes a substrate surface upon which the source gases react to form the epitaxial layer. In order to help control the rate of the growth reaction, the source gases are typically introduced with a carrier gas, with the carrier gas forming the largest volume of the gas flow.

Chemical vapor deposition (CVD) growth processes for silicon carbide have been refined in terms of temperature profiles, gas velocities, gas concentrations, chemistry, and pressure. The selection of conditions used to produce particular epilayers is often a compromise among factors such as desired growth rate, reaction temperature, cycle time, gas volume, equipment cost, doping uniformity, and layer thicknesses.

In particular, and other factors being equal, uniform layer thicknesses tend to provide more consistent performance in semiconductor devices that are subsequently produced from the epitaxial layers. Alternatively, less uniform layers tend to degrade device performance, or even render the layers unsuitable for device manufacture.

In typical CVD processes, however, a phenomenon known as "depletion" occurs and is described as the loss of source gas concentration as the source and carrier gases pass through the reaction vessel. More particularly, in typical CVD systems, the source and carrier gases flow parallel to the substrate and the epitaxial growth surface. Because the source gases react to form the epitaxial layers, their concentration tends to be highest at the gas entry or "upstream" end of the reactor and lowest at the downstream end. In turn, because the concentration of source gases decreases during the travel of the source gases through the reactor, epitaxial layers tend to result that are thicker at the upstream end and thinner at the downstream end. As noted above, this lack of uniformity can be disadvantageous in many circumstances, and is particularly troublesome when thicker epitaxial layers are desired or necessary for certain devices or device structures.

In growth techniques for other semiconductor materials (such as silicon), the problem can be addressed by fairly straightforward techniques such as rotating the substrate (typically a wafer) upon which the epitaxial layer is being grown. Such techniques become much more complex and difficult, however, when carried out at the much higher temperatures required to grow epitaxial layers of silicon carbide. Typically, the susceptors used for silicon carbide growth processes must be formed from highly purified graphite with a high purity coating of silicon carbide. When moving parts are formed from such materials, they tend to be rather complex and prone to generate dust because of the abrasive characteristics of the silicon carbide. Thus, such mechanical and motion-related solutions to the depletion problem are generally unsatisfactory for silicon carbide because of the mechanical difficulties encountered and the impurities that must otherwise be controlled. Accordingly, a need exists for chemical vapor deposition techniques for the epitaxial growth of silicon carbide that produce more uniform epitaxial layers, and yet do so without introducing additional impurities or mechanical complexity to the process.

#### Object and Summary of the Invention

Therefore, it is an object of the present invention to provide a method for obtaining more uniform epitaxial layers of silicon carbide. The invention meets this object with an improved chemical vapor deposition method that increases the uniformity of silicon carbide epitaxial layers and that is particularly useful for obtaining thicker epitaxial layers. The method comprises heating a reactor to a temperature at which silicon carbide source gases will form an epitaxial layer of silicon carbide on a substrate in the reactor; and then directing a flow of source and carrier gases through the heated reactor to form an epitaxial layer of silicon carbide on the substrate with the carrier gases comprising a blend of hydrogen and a second gas in which the second gas has a thermal conductivity that is less than the thermal conductivity of hydrogen so that the source gases deplete less as they pass through the reactor than they would if hydrogen is used as the sole carrier gas. In certain embodiments the second gas is also preferably chemically inert with respect to the chemical vapor deposition reaction.

In another aspect the invention comprises a silicon carbide epitaxial layer with a highly uniform thickness as evidenced by its standard deviation of thickness along its cross section.

The foregoing and other objects and advantages of the invention and the  
5 manner in which the same are accomplished will become clearer based on the following detailed description taken in conjunction with the accompanying drawings in which:

#### Brief Description of the Drawings

Figure 1 is a schematic representation of a chemical vapor deposition system  
10 that is illustrative of those that can be used with the present invention;

Figures 2 and 3 are plots of wafer thickness versus distance from the upstream edge of epitaxial layers grown using prior art techniques;

Figure 4 is a plot of wafer thickness versus distance from the upstream edge of an epitaxial layer grown using the method of the present invention;

15 Figure 5 is a plot of wafer thicknesses versus distance from the upstream edge for the respective epitaxial layers grown on three adjacent wafers in a single reactor using the method of the present invention; and

Figure 6 is a photograph taken with a scanning electron microscope ("SEM") of a cleaved cross-section of a substrate with an epitaxial layer grown according to  
20 the present invention.

#### Detailed Description

The present invention is an improved chemical vapor deposition method that increases the uniformity of silicon carbide epitaxial layers and that is particularly useful for obtaining thicker epitaxial layers. In its method aspects, the invention  
25 comprises heating a reactor to a temperature in which silicon carbide source gases will form an epitaxial layer of silicon carbide on a substrate in the reactor; and thereafter directing a flow of source and carrier gases through the heated reactor to form an epitaxial layer of silicon carbide on the substrate with the carrier gases comprising a blend of hydrogen and a second gas in which the second gas has a  
30 thermal conductivity that is less than the thermal conductivity of hydrogen so that the source gases deplete less as they pass through the reactor than they would if

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hydrogen is used as the sole carrier gas. In certain embodiments, the second gas is preferably chemically inert with respect to the chemical vapor deposition reaction.

In preferred embodiments, the second carrier gas comprises argon. Argon has a number of advantages with respect to the present invention. In particular,  
5 argon has a significantly lower thermal conductivity than does hydrogen. The presence of argon thus moderates the thermal conductivity of the carrier gas which in turn moderates the rate at which the source gases deplete as they move through the reactor.

As another advantage, argon is a "noble" gas meaning that it tends to avoid  
10 reacting with other elements or compounds under almost any conditions. Thus, argon avoids any undesired effect on the epitaxial growth substrate, on the epitaxial layer being grown, or on the other gases in the system. It will be understood, however, that the second carrier gas is not limited to argon, but can be functionally selected to (1) moderate the thermal conductivity of the carrier gas and (2) avoid  
15 undesired reactions with the source gases, the substrate, or the epitaxial layer.

In preferred embodiments, the carrier gases are blended with a greater amount of hydrogen and a lesser amount of the second carrier gas. In most preferred embodiments, where the blend is formed of hydrogen and argon, the blend is preferably at least 75% by volume flow of hydrogen and most preferably up to about  
20 90% by volume flow of hydrogen. Additionally, the blend is not necessarily limited to hydrogen and the gas with the lower thermal conductivity. If desired, another gas can be present (such as helium) provided that the overall blend meets the functional qualifications set forth above.

It will be understood that the volumes as described herein refer to flow  
25 volume on a per minute basis, which is a typical method of measuring the amounts of gases used in chemical vapor deposition systems.

In heating the reactor, the temperature should be high enough for the epitaxial growth of silicon carbide, but lower than the temperature at which the hydrogen carrier gas will tend to etch the silicon carbide. Preferably the system  
30 temperature is maintained at less than about 1800° C and most preferably between about 1500° and 1650° C. At temperatures above about 1800°C, different types of

reactions tend to take place; see e.g., Kordina et al., *Growth of SiC by "Hot-Wall" CVD and HTCVD*, Phys. Stat. 501(B) 202, 321 (1997).

The invention has been found to be particularly useful when the source and carrier gases are directed over a silicon carbide substrate, and most preferably one  
5 selected from the group consisting of the 4H and 6H polytypes, and through the reactor in a direction parallel to the epitaxial growth surface.

Figure 1 is a schematic diagram of a reactor system that is exemplary of those useful with the present invention. The basic structure and arrangement of such a chemical vapor deposition system is generally well known to those of ordinary  
10 skill in this art and can be used by those of ordinary skill in this art to practice the invention without undue experimentation.

In Figure 1 the overall CVD system is broadly designated at 10. The system includes a reactor chamber 11 which contains a susceptor 12. The susceptor 12 is typically heated by an inductive technique (such as radio frequency) using the  
15 electrodes 13 on the exterior of the reactor 11. A substrate 14 rests on the susceptor 12 so that as the radiation from the electrodes 13 heats the susceptor 12, the susceptor heats the substrate 13.

The system includes a supply of source gases and carrier gases schematically diagramed at 15 and 16, respectively. These are directed to the  
20 reactor 11 through an appropriate series of passageways or tubes generally designated at 17 and flow through the reactor as indicated by the curved line 20. It will be understood that the line 20 is simply for illustrative and schematic purposes and is not otherwise representative of the exact flow pattern of gases in a chemical vapor deposition system. The gases then exit through a similar set of tubes or  
25 passageways 21 at the downstream end of the reactor 11.

A number of comparative examples demonstrate the advantages of the present invention and are summarized in Table 1 and Figures 2-5. All of the data was collected from experiments conducted at Cree Research, Inc. in Durham, North Carolina, the assignee of the present invention. As set forth therein, epitaxial layers  
30 of silicon carbide were grown on silicon carbide substrates using either prior techniques (*i.e.*, hydrogen alone as the carrier gas) or the present invention (a blend



of hydrogen and argon as the carrier gas). In each case, the source gases were silane and propane provided at a significantly smaller flow rate than the carrier gas.

Table 1:

Example	Average thickness ( $\mu\text{m}$ )	Standard deviation ( $\mu\text{m}$ )	standard dev/mean (%)	Carrier gas (l/min)
1	28.5	1.61	5.66	44 H <sub>2</sub>
2	58.7	1.33	2.26	60 H <sub>2</sub>
3	26.0	0.61	2.34	40 H <sub>2</sub> + 4 Ar
4	28.8	0	0	60 H <sub>2</sub> + 1 Ar
5	27.5	0	0	60 H <sub>2</sub> + 2 Ar
6	23.8	0	0	60 H <sub>2</sub> + 4 Ar

- 5        The samples were measured using a Scanning Electron Microscope (SEM). The wafers were cleaved along the flow direction. They were then placed on the edge in the SEM. Since the layers were much lower doped than the substrate, contrast between the layer and the substrate was observed (Figure 6). The layer thickness could thus be measured. As shown in Figures 2-5, by measuring the
- 10    thickness in this way on several equidistant points along the cleaved edge, the thickness uniformity could be calculated. There are other techniques for measuring the thickness uniformity, which are not described herein. Removing the data points associated with the epi-crown (e.g., 2 mm closest to the wafer perimeter) is nevertheless common to all techniques in order to reproduce the uniformities shown
- 15    in Table 1.

- The thicknesses of the resulting epitaxial layers were measured at between 10 and 15 positions across the diameter of each resulting wafer. The average (*i.e.*, statistical mean) thickness, the standard deviation, and the percentage deviation (standard deviation expressed as a percentage of the average thickness) were then
- 20    measured for each wafer. In order to prevent edge effects from mischaracterizing the results from the prior art or the invention, either one or two data points were removed from the population prior to the calculation.

- It will be understood that these data points were not removed at random to artificially enhance the results. Instead, data points at one or both of the wafer edges
- 25    were removed in order to avoid including the "epi-crown" that is generally

commonly found in epitaxial growth and that is generally unrelated to the depletion effect.

As Figures 2, 3, and 4 demonstrate, the invention provides a dramatic improvement in the thickness uniformity for epitaxial layers. For example, using  
5 hydrogen alone as the carrier gas (Figures 2 and 3), the percentage deviation was 5.66% and 2.66% with data points measured on the epi crown removed. Using the invention, however, a percentage deviation of 2.34% was obtained for the same hydrogen-alone flow rate that gave the 5.66% deviation. The beneficial effect of the invention is even more evident when used with several wafers that are placed one  
10 behind another in the flow direction of the reactor. Figure 5 illustrates these results and shows that the uniformity for all three wafers is favorably comparable with the uniformity of single wafers grown under the same conditions.

Figure 2 illustrates the edge thickness variations using a prior art technique of hydrogen alone as the carrier gas at a flow rate of 44 liters/minute. Figure 3  
15 illustrates the edge thickness variations using of hydrogen alone at a flow rate of 60 liters/minute. In contrast, Figures 4 and 5 illustrate the improved results using the present invention. In particular, Figure 5 illustrates the advantages of the invention when it is used in a multiple-wafer growth system. As Figure 5 illustrates, the deviation across three wafers using the method of the invention is favorably similar  
20 to the deviation across one wafer (e.g. Figure 3) using the prior art techniques.

Thus, in another aspect, the invention comprises a silicon carbide epitaxial layer with a standard deviation of thickness along its cross section of less than 3% when the data points measured on the epi-crown are dropped from the population. In more preferred embodiments, the standard deviation is less than 2% when the two  
25 data points from the epi-crown are dropped from the population, and in a most preferred embodiment, the standard deviation is less than 1%.

It will be understood, of course, that the term epitaxial layer implies the presence of a substrate, and in preferred embodiments the substrate is a single crystal silicon carbide substrate selected from the group consisting of 4H and 6H  
30 polytypes of silicon carbide.

As used herein, the terms "mean," "standard deviation," "sample," and "population," are used in their normal sense. These values and definitions are well understood within the field of statistics and thus their definition and manner of calculating them will not otherwise be discussed in detail.

5       A blend of hydrogen and argon is preferred over pure argon as a carrier gas because argon is generally relatively hard to purify, is somewhat expensive, and on an empirically observed basis, it seems to harm material quality, while hydrogen seems to purify the growing material. Stated differently, hydrogen as a carrier gas appears to have some scavenging properties. Because of its low thermal  
10 conductivity, a carrier gas of pure argon would also tend to retard growth rates beyond a point that is generally desirable.

The selected proportion of the mix of argon and hydrogen can depend on a number of factors. These factors are, however, relatively well known in the art, and thus once the concept of the invention is understood, the blend can be selected by  
15 those of ordinary skill in the art without undue experimentation. As examples (rather than limitations), however, the amount of argon blended with the hydrogen will depend on items such as the length of the hot zone, the cost of argon, total gas flow, gas purity, and zone temperature. In particular, in most cases, the longer (in distance) the hot zone extends and the higher the expected or required temperature,  
20 the more argon is desirably used to moderate the depletion effects.

Additionally, the price of argon (as noted above, it is expensive) is a practical, although not theoretical, limitation on how much argon is most desirably used.

A third factor is total gas flow. A lower total gas flow is generally  
25 advantageous in a CVD system because it moderates the load on the pumping system, requires less energy and reduces turbulence, and avoids cooling the susceptor.

The purity of argon represents another factor. Because argon cannot be purified as well as hydrogen, the amount used is preferably minimized to  
30 correspondingly minimize any associated impurities. Fortunately, because argon's

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thermal conductivity is approximately one-tenth that of hydrogen's, a relatively small fraction of argon is sufficient to carry out the present invention.

All of the problems associated with uniform thickness control during chemical vapor deposition are exacerbated when thicker layers are being grown.

- 5 Thus, the invention provides an even more noticeable improvement for growing thicker layers. Furthermore, because the invention merely requires blending gases, it avoids the moving parts and mechanical complexity of some other systems for reducing depletion.

- 10 In the drawings and specification, there have been disclosed typical embodiments of the invention, and, although specific terms have been employed, they have been used in a generic and descriptive sense only and not for purposes of limitation, the scope of the invention being set forth in the following claims.

**CLAIMS:**

1. An improved chemical vapor deposition method that increases the uniformity of silicon carbide epitaxial layers and that is particularly useful for obtaining thicker epitaxial layers, the method comprising:
  - 5 heating a reactor to a temperature at which silicon carbide source gases will form an epitaxial layer of silicon carbide on a substrate in the reactor; and
  - directing a flow of source and carrier gases through the heated reactor to form an epitaxial layer of silicon carbide on the substrate;
  - characterized in that:
  - 10 the carrier gases comprise a blend of hydrogen and a second gas in which the second gas has a thermal conductivity that is less than the thermal conductivity of hydrogen so that the source gases deplete less as they pass through the reactor than they would if hydrogen is used as the sole carrier gas.
- 15 2. A chemical vapor deposition method according to Claim 1 wherein the second carrier gas comprises argon.
3. A chemical vapor deposition method according to Claim 1 wherein the first carrier gas is selected from the group consisting of helium and blends of helium  
20 and hydrogen.
4. A chemical vapor deposition method according to Claim 1 wherein the step of blending the carrier gases comprises blending a greater amount of hydrogen with a lesser amount of the second carrier gas.
- 25 5. A method of forming epitaxial layers of silicon carbide on appropriate substrates by chemical vapor deposition, and in which silicon carbide source gases are blended with a first carrier gas and directed into a reactor that is heated to a temperature at which the source gases will react to form an epitaxial layer of silicon  
30 carbide on a substrate in the reactor;
- characterized by:

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blending a second carrier gas with the first carrier gas, and in which the second carrier gas has a thermal conductivity that is less than the thermal conductivity of the first carrier gas, and wherein the second carrier gas is present in an amount that moderates the temperature sufficiently to reduce or eliminate source  
5 gas depletion during the growth of an epitaxial layer of silicon carbide on the substrate, but less than an amount that would reduce the temperature sufficiently to prevent the source gases from reacting to form the epitaxial layer.

6. A chemical vapor deposition method according to Claim 1 or Claim 5  
10 wherein the second carrier gas is chemically inert with respect to the chemical vapor deposition reaction and the silicon carbide.

7. A chemical vapor deposition method according to Claim 1 or Claim 5  
15 wherein the source gases comprise a silicon-containing compound and a carbon-containing compound.

8. A chemical vapor deposition method according to Claim 5 comprising heating the system to a temperature less than about 1800°C.

20 9. A chemical vapor deposition method according to Claim 5 wherein the reactor is heated to a temperature of between about 1500° and 1650°C at which the silane and propane will react to form an epitaxial layer of silicon carbide on a substrate.

25 10. A chemical vapor deposition method according to Claim 1 or Claim 5 comprising directing the gas flow through the reactor in a direction parallel to the epitaxial growth surface.

11. A silicon carbide epitaxial layer;  
characterized by:  
30 a standard deviation of thickness along its cross section of less than three percent excluding the data points measured on the epi-crown.

12. A silicon carbide epitaxial layer according to Claim 11 on a single crystal silicon carbide substrate.

5           13. A silicon carbide epitaxial layer according to Claim 12 wherein said silicon carbide substrate is selected from the group consisting of the 4H and 6H polytypes of silicon carbide.

10           14. A silicon carbide epitaxial layer according to Claim 11 with a standard deviation of thickness along its cross section of less than two percent.

            15. A silicon carbide epitaxial layer according to Claim 11 with a standard deviation of thickness across its cross section of less than 1 percent.

15           16. A silicon carbide epitaxial layer according to Claim 11, Claim 14, or Claim 15 on a single crystal silicon carbide substrate.

            17. A method of forming epitaxial layers of silicon carbide on a plurality of appropriate substrates by chemical vapor deposition comprising:  
20           blending silicon carbide source gases with a first carrier gas;  
            directing the source gases into a reactor that contains a plurality of substrates linearly arranged along the gas flow path in the reactor so that the carrier and source gases flow over the substrates in an upstream to downstream orientation parallel to the epitaxial growth surface; and  
25           heating the reactor to a temperature at which the source gases will react to form an epitaxial layer of silicon carbide on the substrates in the reactor;  
            characterized by:  
            blending a second carrier gas with the first carrier gas, and in which the second carrier gas has a thermal conductivity that is less than the thermal  
30           conductivity of the first carrier gas, and wherein the second carrier gas is present in an amount that moderates the temperature sufficiently to reduce or eliminate source

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gas depletion during the growth of epitaxial layers of silicon carbide on the substrates, but less than an amount that would reduce the temperature sufficiently to prevent the source gases from reacting to form the epitaxial layer.

5           18. A chemical vapor deposition method according to Claim 5 or Claim 17 wherein the first carrier gas comprises hydrogen and the second carrier gas comprises argon.

10           19. A chemical vapor deposition method according to Claim 5 or Claim 17 wherein the step of blending the carrier gases comprises blending a greater amount of the first carrier gas with a lesser amount of the second carrier gas.

15           20. A chemical vapor deposition method according to Claim 18 wherein the blend of hydrogen and argon comprises more than 75 percent by volume flow of hydrogen.

            21. A chemical vapor deposition method according to Claim 20 wherein the blend comprises about 90 percent by volume flow of hydrogen.

20           22. A chemical vapor deposition method according to Claim 17 wherein the source gases comprise silane and propane.

            23. A chemical vapor deposition method according to Claim 22 wherein the reactor is heated to a temperature of between about 1500° and 1650°C.

25           24. A chemical vapor deposition method according to Claim 1, Claim 5, or Claim 17 comprising directing the source and carrier gases over a silicon carbide substrate selected from the group consisting of the 4H and 6H polytypes.



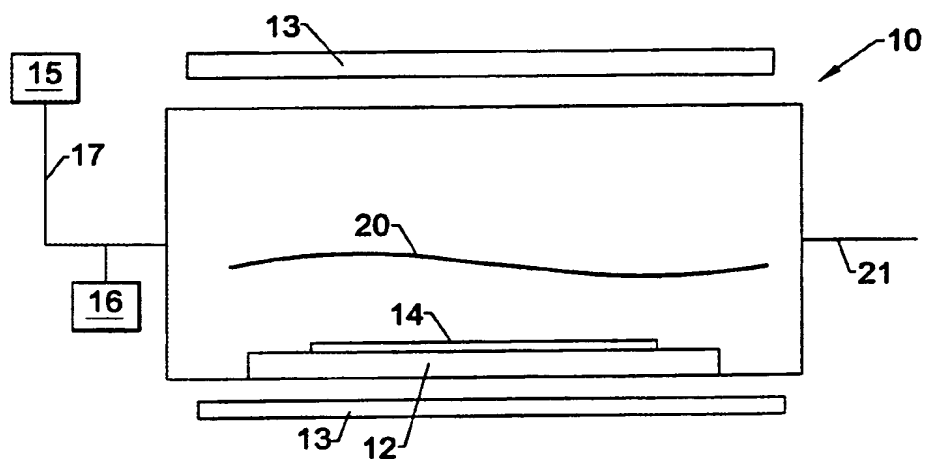
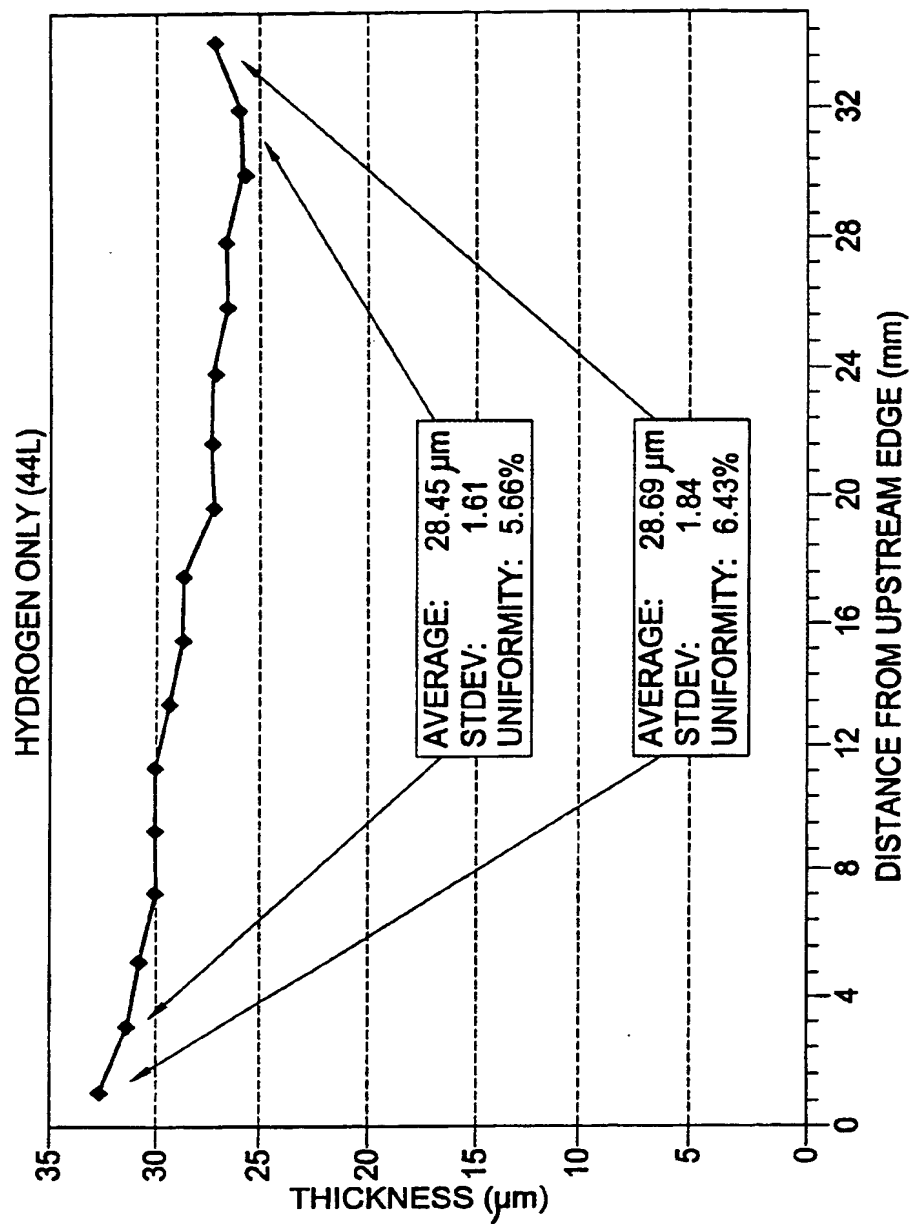


FIG. 1.

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**FIG. 2.**

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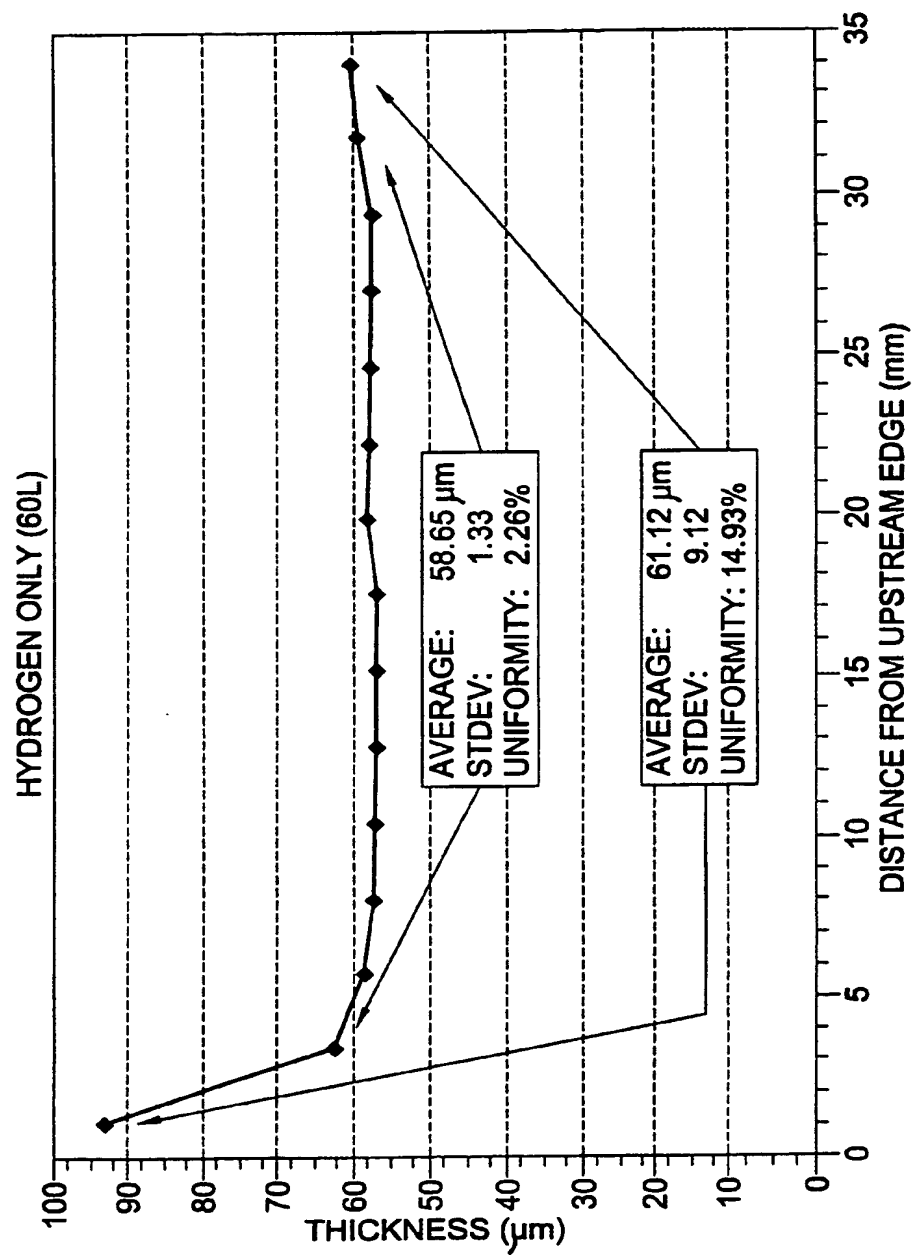


FIG. 3.

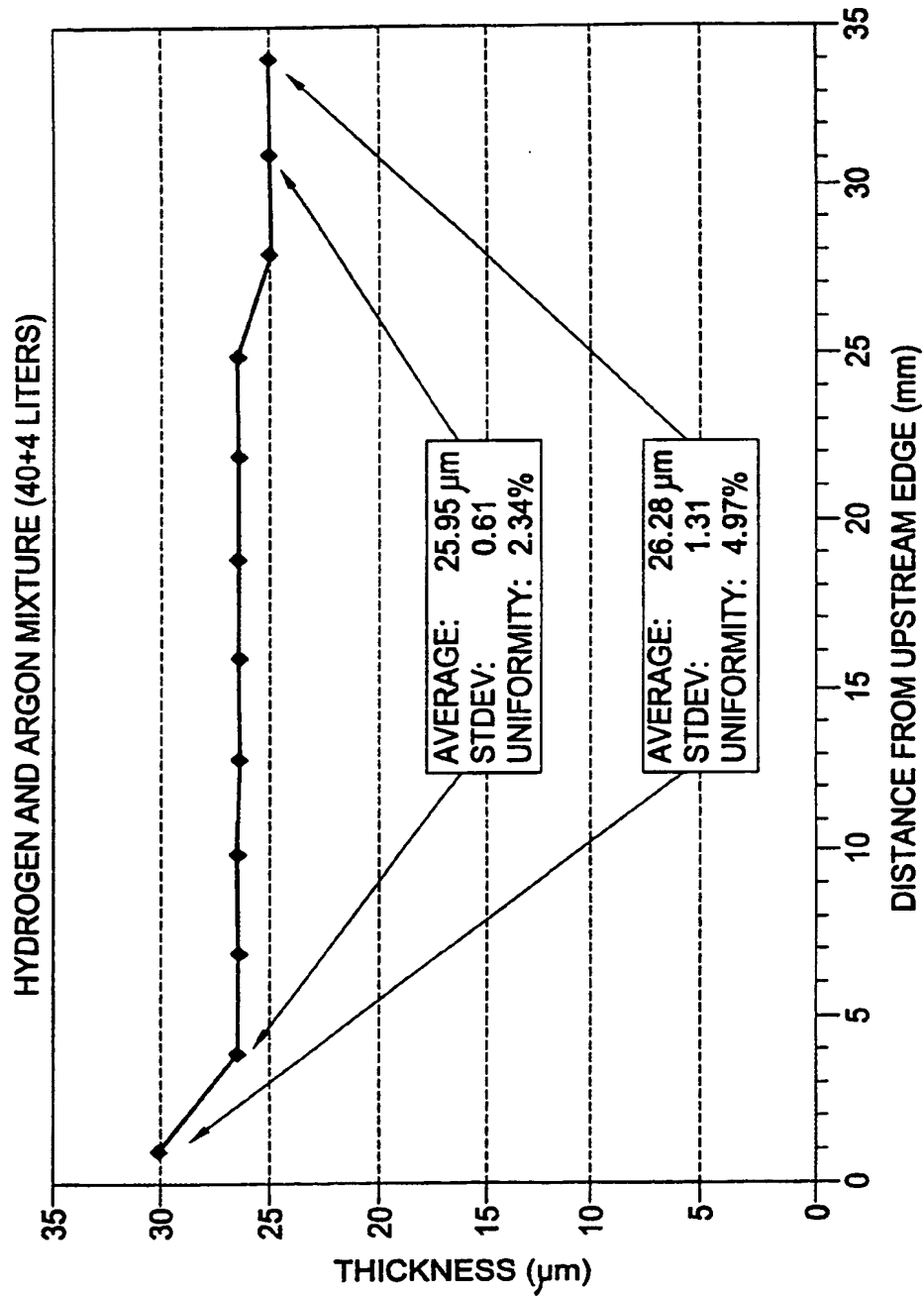


FIG. 4.

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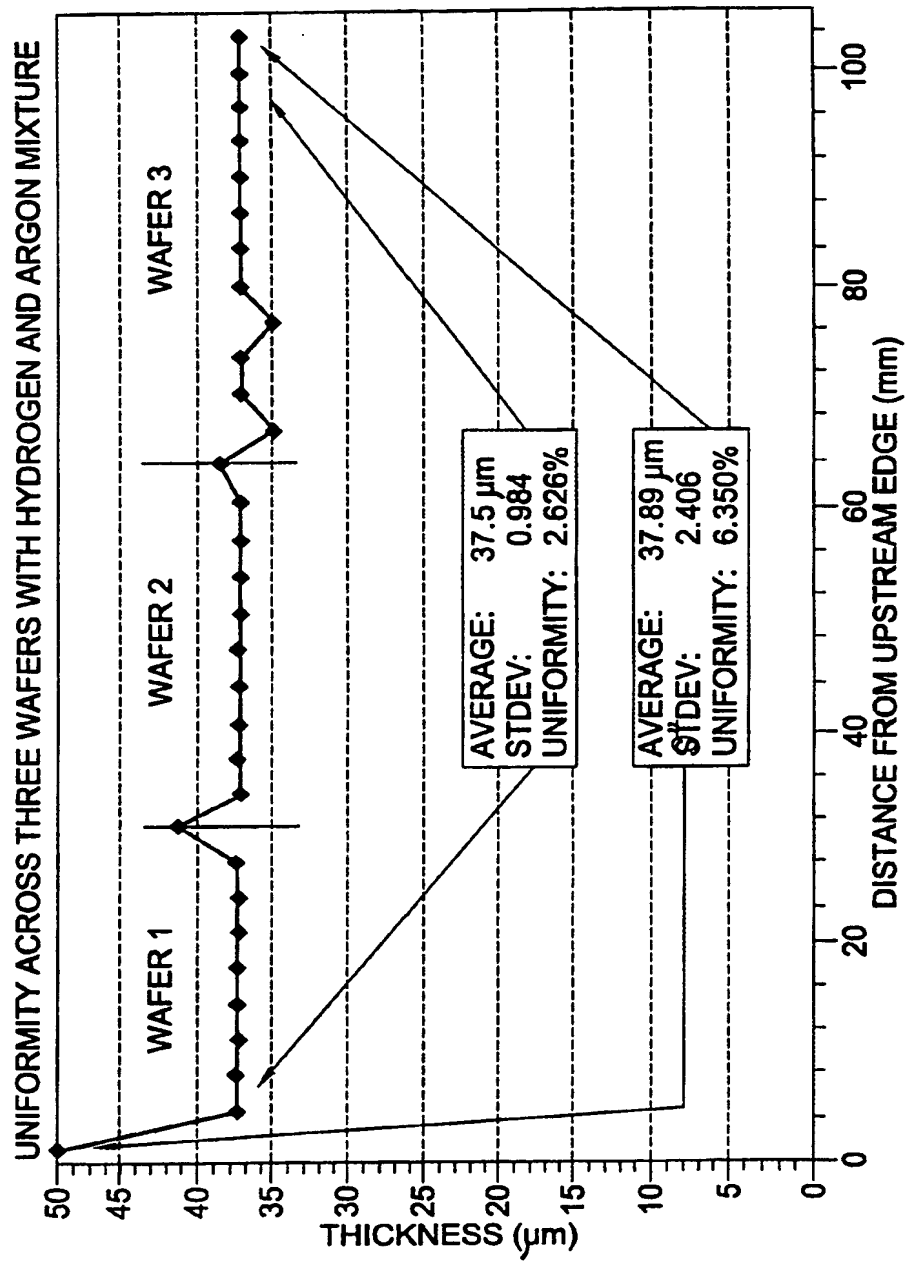


FIG. 5.

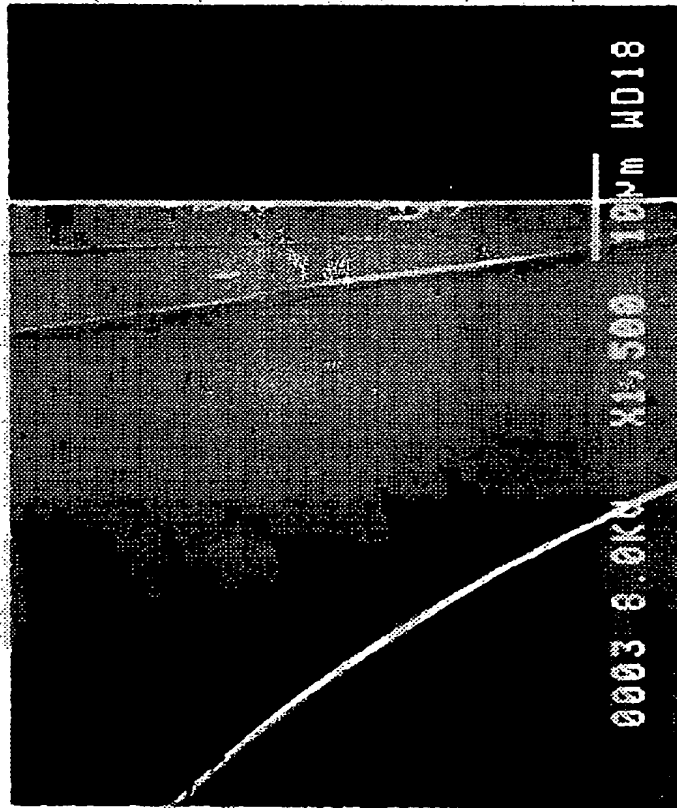


FIG. 6.

# INTERNATIONAL SEARCH REPORT

International Application No

PCT/US 98/26558

## A. CLASSIFICATION OF SUBJECT MATTER

IPC 6 C30B25/02 C30B29/36 C23C16/32

According to International Patent Classification (IPC) or to both national classification and IPC

## B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC 6 C30B C23C

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

## C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	DE 44 32 813 A (SIEMENS AG) 21 March 1996 see the whole document	1-24
X	CHAUDHRY M I ET AL: "THE ROLE OF CARRIER GASES IN THE EPITAXIAL GROWTH OF SS-SIC ON SI BY CVD" JOURNAL OF CRYSTAL GROWTH, vol. 113, no. 1 / 02, 1 August 1991, pages 120-126, XP000259177 see page 125	1,2,11
X	WO 97 01658 A (ABB RESEARCH LTD) 16 January 1997 see page 8, line 33 - page 10, line 10; claims 13-19	1,2
	-/--	

☒ Further documents are listed in the continuation of box C.

☒ Patent family members are listed in annex.

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Date of the actual completion of the international search

14 April 1999

Date of mailing of the international search report

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Cook, S

# INTERNATIONAL SEARCH REPORT

Inter. onal Application No  
PCT/US 98/26558

## C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	PATENT ABSTRACTS OF JAPAN vol. 015, no. 072 (C-0808), 20 February 1991 & JP 02 296799 A (NEC CORP), 7 December 1990 see abstract ----	1,2,11
A	MUENCH VON W ET AL: "NEW SUSCEPTOR ARRANGEMENT FOR THE EPITAXIAL GROWTH OF BETA-SIC ON SILICON" JOURNAL OF CRYSTAL GROWTH, vol. 158, no. 4, 1 February 1996, pages 491-496, XP000588741 see page 493 ----	11
A	PARSONS J D ET AL: "MORPHOLOGICAL STRUCTURE OF SILICON CARBIDE, CHEMICALLY VAPOR DEPOSITED ON TITANIUM CARBIDE, USING ETHYLENE, CARBON TETRACHLORIDE AND SILICON TETRACHLORIDE" JOURNAL OF THE ELECTROCHEMICAL SOCIETY, vol. 141, no. 3, 1 March 1994, pages 771-777, XP000449729 ----	
A	NORDELL N ET AL: "GROWTH OF SIC USING HEXAMETHYLDISILANE IN A HYDROGEN-POOR AMBIENT" APPLIED PHYSICS LETTERS, vol. 64, no. 13, 28 March 1994, pages 1647-1649, XP000441242 ----	1
A	PATENT ABSTRACTS OF JAPAN vol. 011, no. 008 (C-396), 9 January 1987 & JP 61 186288 A (NEC CORP), 19 August 1986 see abstract -----	



# INTERNATIONAL SEARCH REPORT

Information on patent family members

International Application No

PCT/US 98/26558

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